

TECHNICAL DATA DATA SHEET 4659, REV. —

# HERMETIC SCHOTTKY RECTIFIER Low Forward Voltage Drop

#### Features:

- Soft Reverse Recovery at Low and High Temperature
- Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

#### **Maximum Ratings**

Characteristics	<b>Symbol</b>	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	100	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form (Single)	15	Α
Max. Peak One Cycle Non- Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine wave (per leg)	150	Α
Non-Repetitive Avalanche Energy	E <sub>AS</sub>	$T_J = 25  ^{\circ}\text{C}, I_{AS} = 3.0  \text{A}, \\ L = 4.4  \text{mH (per leg)}$	20	mJ
Repetitive Avalanche Current	I <sub>AR</sub>	$I_{AS}$ decay linearly to 0 in 1 $\mu$ s $f$ limited by $T_J$ max $V_A$ =1.5 $V_R$	3.0	Α
Maximum Thermal Resistance	$R_{ ext{ hetaJC}}$	(Single)	1.21	°C/W
Max. Junction Temperature	TJ	-	-65 to +200	°C
Max. Storage Temperature	$T_{stg}$	-	-65 to +200	°C

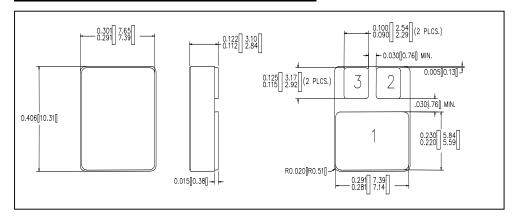
#### **Electrical Characteristics**

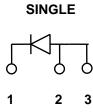
Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	$V_{F1}$	@ 15A, Pulse, T <sub>J</sub> = 25 °C	0.93	V
(per leg)	$V_{F2}$	@ 15A, Pulse, T <sub>J</sub> = 125 °C	0.77	V
Max. Reverse Current	I <sub>R1</sub>	@V <sub>R</sub> = 100V, Pulse,	0.35	mA
		T <sub>J</sub> = 25 °C		
(per leg)	I <sub>R2</sub>	@V <sub>R</sub> = 100V, Pulse,	8.0	mA
		T <sub>J</sub> = 125 °C		
Max. Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C$	500	pF
(per leg)		$f_{SIG} = 1MHz,$		
		$V_{SIG} = 50 \text{mV (p-p)}$		

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# **Mechanical Dimensions: in Inches / mm**

### LCC-5





## **PINOUT TABLE**

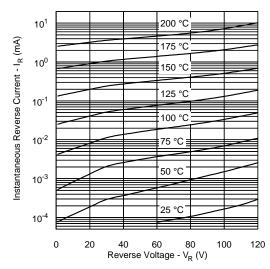
DEVICE TYPE	PIN 1	PIN 2	PIN 3
SINGLE RECTIFIER	CATHODE	ANODE	ANODE

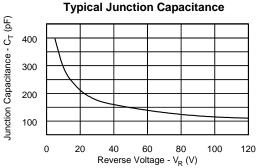
**Note:** The V<sub>f</sub> curves shown are for the SD125SC100 unpackaged die only.

#### **Typical Forward Characteristics**

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#### **Typical Reverse Characteristics**







#### **TECHNICAL DATA**

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